

Silicon NPN Power Transistors

2SD2296

DESCRIPTION

- With TO-3PN package
- High breakdown voltage

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

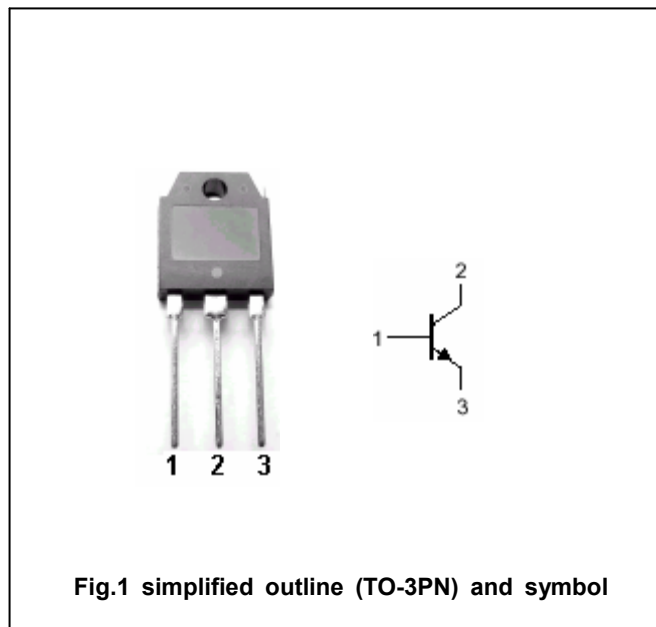


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		5	A
I_{CM}	Collector current -peak		6	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; R _{BE} =∞	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =1.2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =1.2A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1500V ; R _{BE} =0			0.5	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8		30	

Switching times

t _f	Fall time	I _C =4.0A ; I _{B1} =0.8A ; I _{B2} =-1.5A			0.8	μs
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PACKAGE OUTLINE

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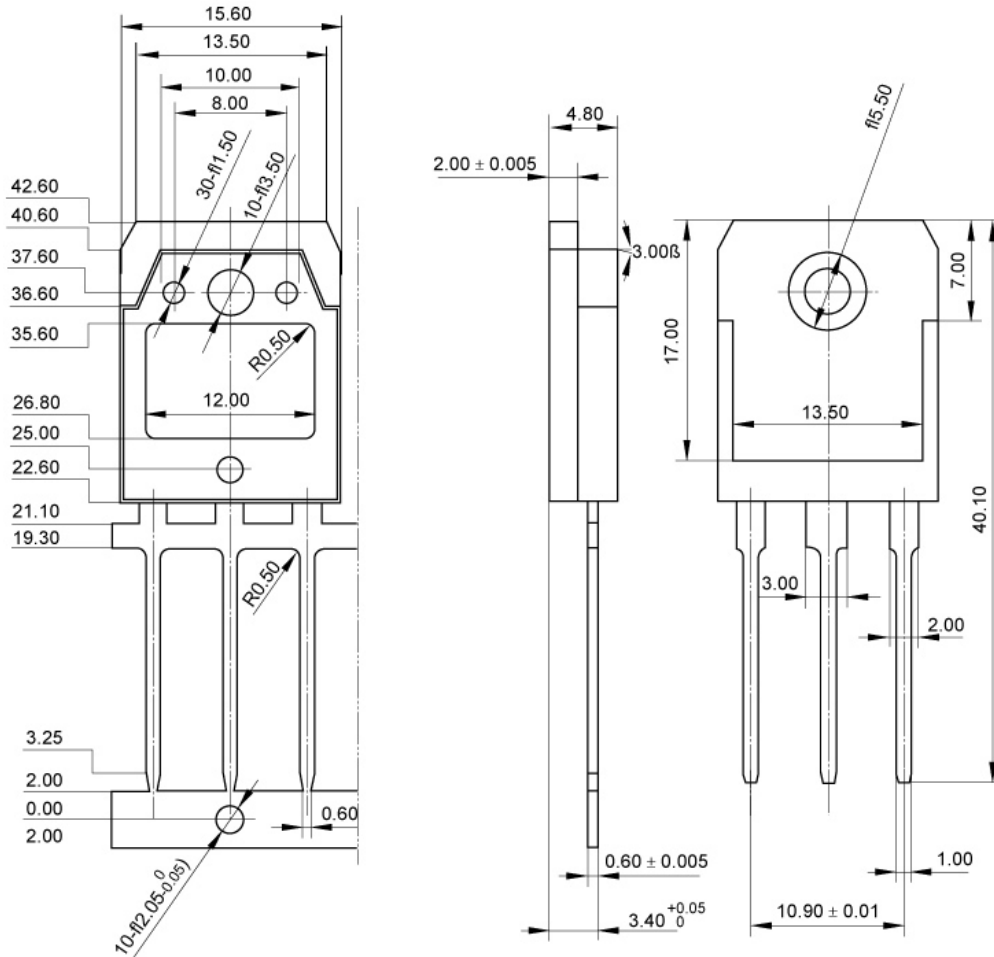


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)